

JFW

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT

Under 37 CFR 1.97(b) or 1.97(c)

Docket No.
YOR920030203US1

In Re Application Of: Stephen W. Bedell, et al.

(16694)

AUG 15 2005

Application No. 10/662,028	Att & TRADEMARKS Filing Date September 12, 2003	Examiner Unknown	Customer No. 23389	Group Art Unit 3661	Confirmation No. 9297
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Title: FORMULATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER

Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:

the statement specified in 37 CFR 1.97(e);

OR

the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
 (Under 37 CFR 1.97(b) or 1.97(c))

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In Re Application of: Stephen W. Bedell, et al. (16694)

AUG 15 2005
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Application No.	Filing Date	Examiner	Customer No.	Group Art Unit	Confirmation No.
10/662,028	September 12, 2005	Unknown	23389	3661	9297

Title: FORMULATION OF A SILICON GERMANIUM-ON-INSULATOR STRUCTURE BY OXIDATION OF A BURIED POROUS SILICON LAYER

Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

A check in the amount of _____ is attached.

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 (Date)

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 Leslie S. Szivos

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 Signature

Dated: August 12, 2005

Leslie S. Szivos
 Registration No. 39,394

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CC:



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Stephen W. Bedell, et al.

Examiner: Unknown

Serial No.: 10/662,028

Art Unit: 3661

Filed: September 12, 2003

Docket: YOR920030203US1 (16694)

For: FORMULATION OF A SILICON
GERMANIUM-ON-INSULATOR
STRUCTURE BY OXIDATION OF A
BURIED POROUS SILICON LAYER

Date: August 12, 2005

Confirmation No: 9297

Mailstop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R §§1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. U.S. Patent No. 4,104,090, issued August 1, 1978, to Pogge, et al.;
2. U.S. Patent No. 5,686,343, issued November 11, 1997, to Lee, et al.;

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on August 12, 2005.

Dated: August 12, 2005



Leslie S. Szivos

3. Mizuno, et al., "High Performance CMOS Operation of Strained-SOI MOSFETs Using Thin Film SiGe-On-Insulator Substrate", 2002 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, June 11-13, 2002, Symposium on VLSI Technology, New York, NY: IEEE, US, June 11, 2002, pp. 106-107, XP001109839;
4. Patent Abstracts of Japan, Vol. 005, No. 181 (E-083), November 20, 1981; and
5. Patent Abstracts of Japan, Vol. 005, No. 117 (E-067), May 18, 1981.

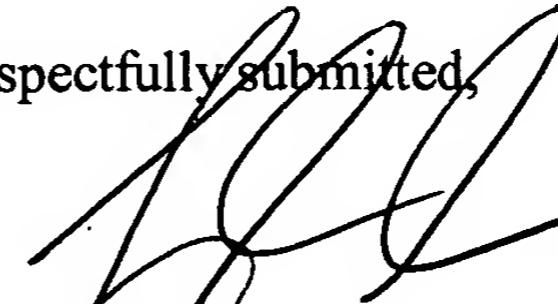
The references were cited in an International Search Report dated May 17, 2005 received from the European Patent Office. Applicants are submitting copies of references 3-5, together with a copy of the International Search Report. The relevance of each the above-identified references has been described in the Search Report as defining the general state of the art.

In the event an Action on the merits crosses in the mail, the applicants state the following:

"That each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement."

Inasmuch as this Information Disclosure Statement is being submitted in accordance with the schedule set out in 37 C.F.R. § 1.97(b), no statement or fee is required.

Respectfully submitted,

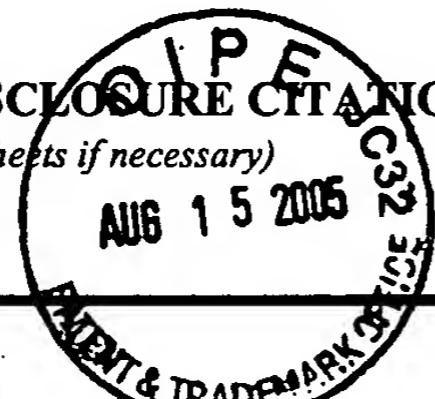

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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

Y0R920030203US1 (16694)

Application Number

10/662,028

Applicant(s)

Stephen W. Bedell, et al.

Filing Date

September 12, 2003

Group Art Unit

3661

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		4,104,090	08/01/1978	Pogge, et al.			
		5,686,343	11/11/1997	Lee, et al.			

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

		Mizuno, et al., "High Performance CMOS Operation of Strained-SOI MOSFETs Using Thin Film SiGe-On-Insulator Substrate", 2002 Symposium on VLSI Technology, Digest of Technical Papers, Honolulu, June 11-13, 2002, Symposium on VLSI Technology, New York, NY: IEEE, US, June 11, 2002, pp. 106-107, XP001109839
		Patent Abstracts of Japan, Vol. 005, No. 181 (E-083), November 20, 1981

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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